Abstract of the Disclosure

A method of fabricating a contact pad of a semiconductor device is disclosed. The method includes forming a stopping layer over the semiconductor substrate. An interdielectric layer is formed over the stopping layer, and the interdielectric layer is planarized to expose at least a gate upper dielectric layer by using a material which exhibits a high-polishing selectivity with respect to the interdielectric layer. The interdielectric layer is etched in a region in which a contact pad will be formed on the semiconductor substrate. A conductive material is deposited on the semiconductor substrate. Finally, planarizing is carried out using a material which exhibits a high-polishing selectivity of the upper dielectric layer with respect to the conductive material.